ADE-208-039D(Z)

HSM276S
Silicon Schottky Barrier Diode for Balanced Mixer

HITACHI

Rev.4
Aug. 1994

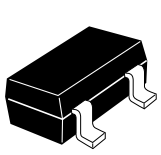
Features

- High forward current, Low capacitance.
- HSM276S which is interconnected in series configuration is designed for balanced mixer use
- MPAK package is suitable for high density surface mounting and high speed assembly.

Ordering Information

Type No.	Laser Mark	Package Code
HSM276S	C 2	MPAK

Pin Arrangement



(Top View)

1 Cathode 2
2 Anode 1
3 Cathode 1
Anode 2

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Value	Unit
Reverse voltage	V_R	3	V
Average forward current	I_o*	30	mA
Junction temperature	T_j	100	°C
Storage temperature	T_{stg}	-55 to +100	°C

* Per one device

Electrical Characteristics (Ta = 25°C) *

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse voltage	V_R	3.0	—	—	V	I_R = 1 mA
Reverse current	I_R	—	—	50	µA	V_R= 0.5 V
Forward current	I_F	35	—	—	mA	V_F= 0.5 V
Capacitance	C	—	—	0.90	pF	V_R = 0.5 V, f = 1 MHz
Capacitance deviation	ΔC	—	—	0.10	pF	V_R = 0.5 V, f = 1 MHz
ESD Capability	—	30	—	—	V	** C=200pF, Both forward and reverse direction 1 pulse

* Per one device
** Failure Criterrion ; $I_R \geq 100\mu A$ at V_R = 0.5V

HSM276S

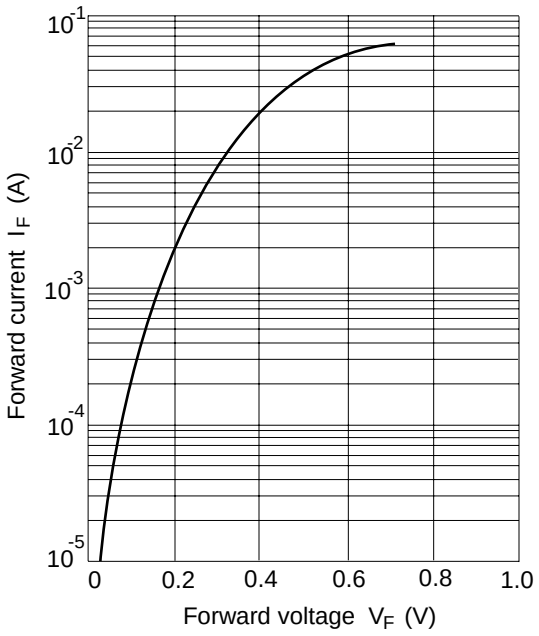


Fig.1 Forward current Vs. Forward voltage

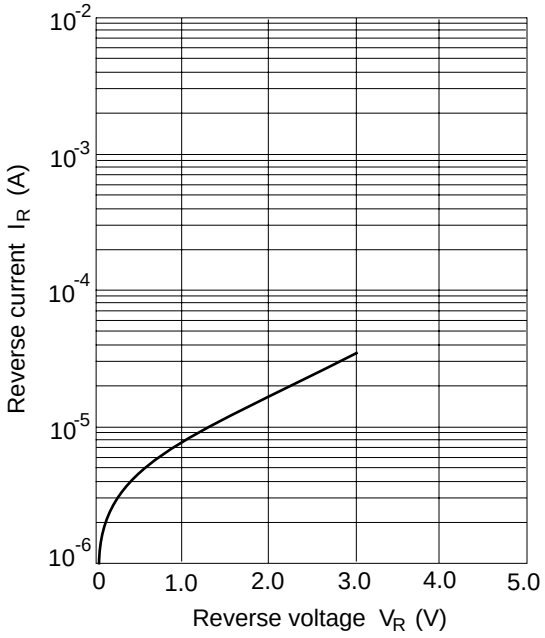


Fig.2 Reverse current Vs. Reverse voltage

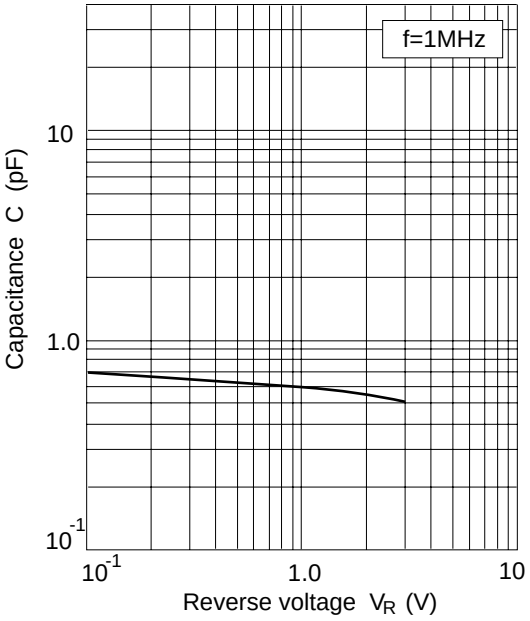
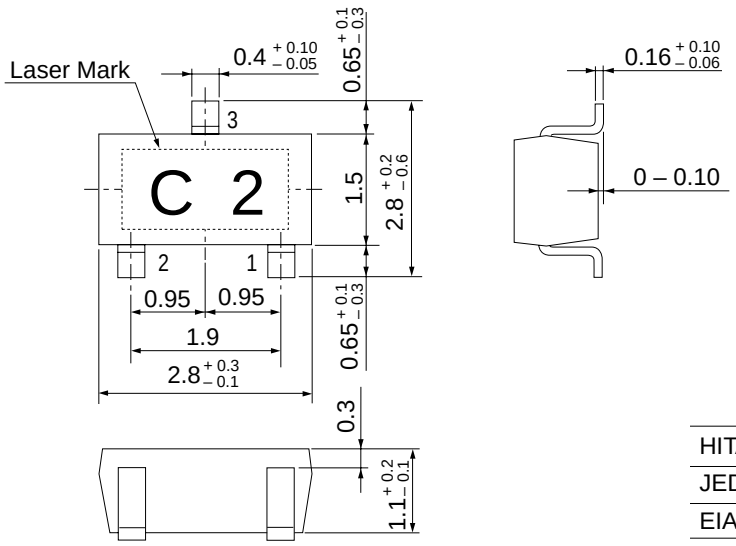


Fig.3 Capacitance Vs. Reverse voltage

Package Dimensions

Unit: mm



1 Cathode 2
2 Anode 1
3 Cathode 1
Anode 2

HITACHI Code	MPAK(1)
JEDEC Code	—
EIAJ Code	SC-59A
Weight (g)	0.011